

INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous) Dundigal, Hyderabad - 500 043

ELECTRONICS AND COMMUNICATION ENGINEERING

DEFINITIONS AND TERMINOLOGY QUESTION BANK

| Course Name | | : | VLSI DESIGN | |
|----------------|---|---|--|--|
| Course Code | | : | AEC017 | |
| Program | | : | B.Tech | |
| Semester | | : | VII | |
| Branch | | : | Electronics and Communication Engineering | |
| Section | · | : | A, B, C,D | |
| Academic Year | | : | 2019 - 2020 | |
| Course Faculty | | : | Dr. V Vijay, Associate Professor Dr. M Manisha, Associate Professor Ms. K S Indrani, Assistant Professor Mr. V R Seshagiri Rao, Associate professor | |

OBJECTIVES:

| Ι | Have skills to use concepts of MOS devices for the fabrication of integrated chips (IC's). |
|-----|---|
| II | Familiarize CMOS layout rules in the placement and routing of transistors and interconnect, and |
| | to verify the functionality, timing, power, and parasitic effects. |
| III | Demonstrate the ability to design static CMOS combinational and sequential logic at the |
| | transistor level, including mask layout. |
| IV | Focus in selecting appropriate building blocks of data path for given system. |

DEFINITIONS AND TERMINOLOGY QUESTION BANK

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|--------------------------------------|--|---------------------|------|-------|-----------|
| | | UNIT-I | | | | |
| 1 | What is depletion mode? | In this MOSFET device is normally ON at zero gate– source voltage. | Understand | CO 1 | CLO 1 | AEC017.01 |
| 2 | What is enhancement mode? | These devices are off at zero gate–source voltage, NMOS can be turned on by pulling the gate voltage higher than the source voltage, PMOS can be turned on by pulling the gate voltage lower than the source voltage. | Understand | CO 1 | CLO 1 | AEC017.01 |
| 3 | What are the applications of MOSFET? | All digital and Analog circuits | Understand | CO 1 | CLO 1 | AEC017.01 |
| 4 | How MOSFET is better than BJT? | MOSFETs are better in terms of power consumption. As the supply voltage is less in MOSFETs when compared to BJTs, power consumption is also very less. | Understand | CO 1 | CLO 1 | AEC017.01 |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|------------------|---------------------------------|---------------------|----------|---------------|-----------|
| 5 | What is pinch | Pinch off voltage is the drain | Understand | CO 1 | CLO 1 | AEC017.01 |
| | off? | to source voltage after which | | | | |
| | | the drain to source current | | | | |
| | | becomes almost constant and | | | | |
| | | MOSFET enters into | | | | |
| | | saturation region and is | | | | |
| | | defined only when gate to | | | | |
| | | source voltage is zero. | | | | |
| 6 | What is latch | Latch up is defined as the | Understand | CO 1 | CLO 2 | AEC017.02 |
| | up? | generation of a low- | | | | |
| | * | impedance path in CMOS | | | | |
| | | between the power supply | | | | |
| | | (VDD) and the ground (GND) | | | | |
| | | due to the interaction of | | - | | |
| | - | parasitic PNP and NPN | 1 T . I . | | | |
| | | bipolar junction transistors | | \sim | | |
| | | (BJTs). | | | | |
| 7 | What is body | Body effect refers to the | Remember | CO 1 | CLO 2 | AEC017.02 |
| | effect? | change in the transistor | | | | |
| | | threshold voltage (VT) | | | | |
| | | resulting from a voltage | | | | |
| | | difference between the | | | | |
| | | transistor source and body. | | | | |
| 8 | What is triode | The triode region is the | Remember | CO 1 | CLO 1 | AEC017.01 |
| | region? | operating region where the | | | | |
| | | inversion region exists and | | | | |
| | | current flows, but this region | _ | | | |
| | | has begun to taper near the | | | | |
| | | source. | | | | |
| 9 | What do u mean | It is a region in which | Remember | CO 1 | CLO 1 | AEC017.01 |
| | by cut-off | transistor remains OFF and | | | | |
| | region? | needed some threshold voltage | | | | |
| | 5 | to operate or to move | | | | 100 |
| 10 | What is linear | There "linear" can mean | Understand | CO 1 | CLO 1 | AEC017.01 |
| | region in MOS | "roughly linear current with | | - | - C |) |
| | transistor? | applied voltage", which also | | | | |
| | 0 | means the MOSFET is acting | | 7 | | |
| | 0 | like a resistor as opposed to | | | | |
| | | more like a current source. | | ~~ · · | CT 0.0 | |
| 11 | Define sub- | The supply voltage which is | Understand | CO 1 | CLO 2 | AEC017.02 |
| | threshold | less than threshold voltage is | | 1 | | |
| 10 | voltage | called sub-threshold voltage | TT 1 . 1 | 00.1 | | |
| 12 | Define sub- | The region of operation of a | Understand | 001 | CLO 2 | AEC017.02 |
| | threshold region | MOSFET below its threshold | 111 | 1 A A | | |
| | | voltage is called sub threshold | | | | |
| | | region. It is also known as | | | | |
| 10 | Define and | weak inversion region | I In damate 1 | CO 1 | CLOC | AEC017.02 |
| 15 | Define super | The region of operation of a | Understand | 01 | CLO 2 | AEC017.02 |
| | threshold region | MOSFET above its infestion | | | | |
| | | throshold region It is also | | | | |
| | | known as strong inversion | | | | |
| | | region | | | | |
| 14 | List out Short | 1 Threshold voltage roll | Understand | CO 1 | CLO 3 | AEC017.03 |
| 14 | channel effects | off | Understand | 01 | CLO 5 | ALC017.05 |
| | of MOSEET | 2 Sub-threshold current | | | | |
| | OT MODILI | 3 Drain induced barrier | | | | |
| | | lowering (DIRI) | | | | |
| | | 4 Hot carrier effect | | | | |
| | | 5 Impact Ionization | | | | |
| L | 1 | - The contraction | I | | | 1 |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|------------------|-----------------------------------|---------------------------------------|------|-------|-----------|
| | | 6 Velocity saturation | | | | |
| | | 7 Gate Induced Drain | | | | |
| | | Leakage (GIDL) | | | | |
| 15 | Define threshold | The voltage at which the | Understand | CO 1 | CLO 2 | AEC017.02 |
| | voltage? | conduction starts is called | | | | |
| 16 | What is Dusin | threshold voltage. | I I a de note a d | CO 1 | CIO2 | AEC017.02 |
| 10 | what is Drain | Drain-induced Darrier | Understand | 01 | CLU 3 | AEC017.03 |
| | lowering | channel effect in MOSEETs | | | | |
| | lowering | referring originally to a | | | | |
| | | reduction of threshold voltage | | | | |
| | | of the transistor at higher drain | | | | |
| | | voltages. | | | | |
| 17 | What is GIDL | Gate-induced drain leakage, | Understand | CO 1 | CLO 3 | AEC017.03 |
| | | GIDL is induced by band-to- | | | | |
| | | band tunneling effect in strong | | | | |
| | | accumulation mode and | | | | |
| | | generated in the gate-to-drain | | | | |
| | | overlap region. | | | | |
| 18 | What is Hot | Hot carrier injection in | Understand | CO 1 | CLO 1 | AEC017.01 |
| | carrier effect | MOSFETs occurs when a | | | | |
| | | carrier from Si channel is | | | | |
| 10 | XX 71 1 | injected into the gate oxide. | | 00.1 | | AEC017.01 |
| 19 | Why does | Due to doping in poly silicate | Understand | COT | CLO I | AEC017.01 |
| | in MOSEET2 | dened mostly) used in gets of | | | | |
| | III MOSFET ? | MOSEET tunnel effect occurs | | | | |
| | | from gate to channel / source / | | | | |
| | | drain in forward bias and | | | | |
| | | between gate to source / drain | | | | |
| | | in reverse bias. | | | | |
| 20 | What is Sub- | An effect that is exacerbated | Understand | CO 1 | CLO 2 | AEC017.02 |
| | threshold | by short channel designs is the | | _ | | 1 |
| | current | sub-threshold current which | | | | |
| | | arises from the fact that some | | - | - C |) |
| | | electrons are induced in the | | 1 | - | |
| | | channel even before strong | | | 4 | |
| | | inversion is established. For | | | | |
| | | the low electron concentration | | | 100 | |
| | | (typically of sub-threshold | | | | |
| | | current (proportional to carrier | | 23 | | |
| | | gradients) to dominate over | - | ~ | | |
| | | drift currents (proportional to | | | | |
| | | carrier concentrations). For | 1 1 1 | | | |
| | | very short channel lengths, | · · · · · · · · · · · · · · · · · · · | | | |
| | | such carrier diffusion from | | | | |
| | | source to drain can make it | | | | |
| | | impossible to turn off the | | | | |
| | | device below threshold. The | | | | |
| | | sub-threshold current is made | | | | |
| | | worse by the DIBL effect | | | | |
| | | which increases the injection | | | | |
| 21 | How mobility | Lateral Field Effect: In case of | Understand | CO 1 | CIO 2 | AEC017.02 |
| 21 | degradation | short channels as the lateral | Understand | CUI | CLO 3 | AEC017.03 |
| | occurs in | field is increased the channel | | | | |
| | MOSFET? | mobility becomes field- | | | | |
| | | dependent and eventually | | | | |
| | | velocity saturation occurs. | | | | |

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|------|--------------------------|---|---------------------|-------------|--------|-----------|
| | | This results in current | | | | |
| | | saturation. | | | | |
| | | Vertical Field Effect: As the | | | | |
| | | vertical electric field also | | | | |
| | | increases on shrinking the | | | | |
| | | channel lengths, it results in | | | | |
| | | scattering of carriers near the | | | | |
| | | surface. Hence the surface | | | | |
| | | mobility reduces. Thus for | | | | |
| | | short channels, the mobility | | | | |
| | | degradation which occurs due | | | | |
| | | to velocity saturation and | | | | |
| - 22 | X71 | scattering of carriers. | | CO 1 | 01.0.2 | AEC017.02 |
| 22 | what is $V_{\rm T}$ roll | The variations in threshold | Understand | 001 | CLO 3 | AEC017.03 |
| | 011? | voltage with respect to | | | | |
| | | channel length in short | | | | |
| 23 | What is Drain | When the drain is at high | Domombor | CO 1 | CLO 3 | AEC017.02 |
| 23 | punch through | enough voltage with respect to | Kemember | 01 | CLO 5 | AEC017.05 |
| | punch unough | the source the depletion | | | | |
| | | region around the drain may | | | | |
| | | extend to the source causing | | | | |
| | | current to flow irrespective of | | | | |
| | | gate voltage (i.e. even if gate | | | | |
| | | voltage is zero). This is known | | | | |
| | | as Drain Punch Through | | | | |
| | | condition | | | | |
| 24 | What is aspect | The ratio of width to length | Remember | CO 1 | CLO 1 | AEC017.01 |
| | ratio | (W/L) in a MOSFET is called | | | | |
| | | aspect ratio or β ratio or | | | | |
| | | transistor ratio | | | | |
| 25 | Write down | W W V V | Remember | CO 1 | CLO 1 | AEC017.01 |
| | drain current | $I_{D} = \mu_{n} C_{OX} - \frac{1}{L} (V_{GS} - V_{T}) V_{DS} - \frac{1}{2}$ | | | | 1 |
| | equation of | | | | | |
| | NMOS in linear | $JOT \ \mathbf{v}_{GS} > \mathbf{v}_{T}, \mathbf{v}_{DS} \leq \mathbf{v}_{GS} - \mathbf{v}_{T}$ | | - | - C |) |
| | region of | | | | | |
| 2.5 | operation | | D 1 | GO 1 | CT 0 1 | |
| 26 | What is channel | Channel length modulation | Remember | COT | CLO I | AEC017.01 |
| | length | (CLM) is a shortening of the | | | Sec. 1 | |
| | modulation | length of the inverted channel | | | | |
| | | region with increase in drain | | ~~ | | |
| 27 | What is lookage | The surrant in a MOSEET | Understand | CO 1 | CLO 1 | AEC017.01 |
| 21 | w nat is leakage | when the MOSEET is in OEE | Understand | 01 | CLU I | AEC017.01 |
| | current? | state. It is also known as static | | · · · · · | | |
| | | current / OFE current | | | | |
| 28 | State Moore's | The number of transistors per | Remember | CO 1 | CLO 1 | AEC017.01 |
| 20 | law | square inch on integrated | Kenteniber | 001 | CLU I | ALCOI7.01 |
| | 14 ** | circuits had doubled every | | | | |
| | | vear since the integrated | | | | |
| | | circuit was invented. | | | | |
| 29 | Why Moore's | Moore's law is ending due to | Remember | CO 1 | CLO 1 | AEC017.01 |
| - | law is ending? | continually shrinking of the | | | | |
| | - O | size of components on a chip | | | | |
| | | (due to technology scaling) | | | | |
| 30 | What is Tick | In technology terms, tick-tock | Remember | CO 1 | CLO 1 | AEC017.01 |
| | Tock model? | typically refers to Intel's | | | | |
| | | model of releasing | | | | |
| | | new processor families each | | | | |
| | | year, with the "tick" applying | | | | |

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| | _ | to processors fabricated on a | | | | |
| | | smaller die shrink and the | | | | |
| | | "tock" representing processors | | | | |
| | | that is based on a new | | | | |
| | | processor micro-architecture. | | | | |
| | | The "tick" processors feature | | | | |
| | | enhanced performance and | | | | |
| | | energy efficiency on a smaller, | | | | |
| | | while the "tock" processors | | | | |
| | | typically optimize the value of | | | | |
| | | the increased number of | | | | |
| | | transistors available from the | | | | |
| | | "tick" release and also | | - | | |
| | - | integrate the latest technology | 1.1 | | | |
| | | updates available. | |) | | |
| 31 | What is | Technology scaling is | Understand | CO 1 | CLO 3 | AEC017.03 |
| | technology | reduction of the lateral and | | | | |
| | scaling | vertical dimensions of | | | | |
| | | transistors. The supply voltage | | | | |
| | | (VDD) is scaled down to | | | | |
| | | to maintain device reliability | | | | |
| 32 | What is ITRS? | The International Technology | Remember | CO 1 | CLO 1 | AEC017.01 |
| 52 | What is it is. | Roadmap for Semiconductors | Remember | COT | CLUI | ALCOI7.01 |
| 33 | What is the | Power reduces | Understand | CO 1 | CLO 2 | AEC017.01 |
| | impact of down | | | | | |
| | scaling the | | | | | |
| | MOSFET on | | | | | |
| | power | | | | | |
| | dissipation? | | | | 61 6 6 | |
| 34 | What is the | Propagation delay increases | Understand | CO 1 | CLO 2 | AEC017.01 |
| | impact of down | | | | | C |
| | MOSEET on | | | _ | - | |
| | propagation | | | | | 8 |
| | delav? | Constituted in the local lines | Contraction of the local division of the loc | 1 C - C | ~ | |
| 35 | What is the | Area reduces | Understand | CO 1 | CLO 3 | AEC017.03 |
| | impact of down | | 1 | · · · · | - | |
| | scaling the | | | | 10 | |
| | MOSFET on | | | | S | |
| | area? | | | 6.7 | | |
| 36 | What is velocity | Saturation velocity is the | Understand | CO 1 | CLO 3 | AEC017.03 |
| | saturation? | maximum velocity a charge | | | | |
| | | carrier in a semiconductor, | | | | |
| | | in the presence of very | | | | |
| | | high electric fields When this | | | | |
| | | happens, the semiconductor is | | | | |
| | | said to be in a state of velocity | | | | |
| | | saturation | | | | |
| 37 | What is Bi- | Bi-CMOS technology is a | Remember | CO 1 | CLO 1 | AEC017.02 |
| | CMOS | combination of Bipolar and | | | | |
| | technology? | CMOS technologies. | | | | |
| 38 | What is | Mobility is the measure of | Remember | CO 1 | CLO 1 | AEC017.01 |
| | mobility? | how quickly an electron can | | | | |
| | | semiconductor in presence of | | | | |
| | | electrical field. | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|------------------|---------------------------------------|---------------------|--------|---------------------------------------|------------|
| 39 | What is totem | Totem-pole output, also | Remember | CO 1 | CLO 1 | AEC017.02 |
| | pole | known as a push-pull output, | | | | |
| | configuration? | is a type of electronic circuit | | | | |
| | | and usually realized as a | | | | |
| | | complementary pair of | | | | |
| | | transistors. The High and Low | | | | |
| | | determined The output of | | | | |
| | | high level is 10 V max low | | | | |
| | | level is 0.5 V min. | | | | |
| | | | | L | | <u> </u> |
| | | UNIT-II | L | | | |
| 1 | Define dry | Dry oxidation means, it is | Remember | CO 2 | CLO 5 | AEC017.05 |
| | oxidation | oxidized with oxygen. | | | | |
| | process | $Si + O_2 \rightarrow SiO_2$ | | | | |
| 2 | Define wet | Wet oxidation means the | Understand | CO 2 | CLO 5 | AEC017.05 |
| | oxidation | silicon is oxidized with stream | | | | |
| | process | or water vapor. | | | | |
| 2 | What are the | $Si + 2H_2O \rightarrow SiO_2 + 2H_2$ | Derrort | 60.2 | CLOS | AEC017.05 |
| 3 | what are the | 1. Thermal oxidation | Remember | CO 2 | CL05 | AEC017.05 |
| | amerent | 2. Electrochemical oxidation | | | | |
| | processes? | | | | | |
| 4 | What is | Exposing photoresist through | Remember | CO_2 | CLO 1 | AEC017.02 |
| | masking? | n-well mask is called masking | Remember | 002 | CLO I | 1112011.02 |
| 5 | What is | Chemical vapor | Understand | CO 2 | CLO 1 | AEC017.01 |
| - | Chemical Vapor | deposition (CVD) is a vacuum | | 001 | | 1120017101 |
| | Deposition | deposition method used to | | | | |
| | (CVD) process | produce high quality, high- | | | | |
| | | performance, solid materials. | | | | |
| | | In typical CVD, the wafer | | | | |
| | - | (substrate) is exposed to one | | | | - |
| | | or more volatile precursors, | | | | |
| | 0 | which react and/or decompose | | | 0 | |
| | ~ | produce the desired deposit | | · · · | · · · · · | e |
| 6 | What is | In fabrication processing the | Understand | CO_2 | CLOS | AFC017.05 |
| 0 | diffusion | term "diffusion" usually refers | Onderstand | 02 | CLO J | ALCOIT.05 |
| | unrusion | to the entire process of adding | | | Sec. 1 | |
| | -7 | a dopant to the surface of | | | - N | |
| | | wafer at high temperature. | | ~~~ | · · · · · · · · · · · · · · · · · · · | |
| 7 | What is oxide | Stripping off the remaining | Remember | CO 2 | CLO 5 | AEC017.05 |
| | stripping | oxidation layer is called oxide | . 0 | | | |
| | | stripping | | | | |
| 8 | What is | Aluminum is sputtered on the | Remember | CO 2 | CLO 5 | AEC017.05 |
| | Metallization | whole water | D 1 | | <u> </u> | |
| 9 | What is | In physics, sputtering is a | Remember | CO 2 | CLO 5 | AEC017.05 |
| | sputtering | phenomenon in which | | | | |
| | | solid material are ejected from | | | | |
| | | its surface after the material is | | | | |
| | | itself bombarded by energetic | | | | |
| | | particles of a plasma or gas. | | | | |
| 10 | What is etching? | Etching is used in | Remember | CO 2 | CLO 5 | AEC017.05 |
| | 5 | microfabrication to chemically | | | | |
| | | remove layers from the | | | | |
| | | surface of a wafer during | | | | |
| | | manufacturing. Etching is a | | | | |
| | | critically important process | | | | |

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| | | module, and every wafer | | | | |
| | | undergoes many etching steps | | | | |
| | | before it is complete. | | | | |
| 11 | What is ion | Ion implantation is a low- | Understand | CO 2 | CLO 5 | AEC017.05 |
| | implantation | temperature process by which | | | | |
| | | ions of one element are | | | | |
| | | accelerated into a solid target, | | | | |
| | | thereby changing the physical, | | | | |
| | | chemical, or electrical | | | | |
| | | properties of the target. | | | | |
| 12 | What is Twin | The process of creating both a | Understand | CO 2 | CLO 5 | AEC017.05 |
| | Well/Tub | p-well and an n-well for the n- | | | | |
| | Technology | MOSFET's and p-MOSFET | | | | |
| | | respectively is twin | | - | | |
| | | well or twin tub technology. | | | | |
| | | Such a choice means that the | | | | |
| | | process is independent of the | | | | |
| | | dopant type of the starting | | | | |
| | | substrate (provided it is only | | | | |
| | | lightly doped). | | | | |
| 13 | What is | Lithography is the process of | Understand | CO 2 | CLO 5 | AEC017.05 |
| | lithography? | transferring circuit pattern | | | | |
| | | directly on to the silicon | | | | |
| | | wafer. But first, the designer | | | | |
| | | must have designed the | | | | |
| | | circuit, determined the size of | | | | |
| | | various circuit elements down | | | | |
| | | to transistor bases to lead | | | | |
| | | width, and their exact | | | | |
| | | positions on the chip. | | | | |
| 14 | What is SOI | Silicon on insulator (SOI) | Understand | CO 2 | CLO 5 | AEC017.05 |
| | CMOS | CMOS technology refers to | | | | |
| | technology? | the use of a layered silicon- | | | | 100 |
| | | insulator-silicon substrate in | | | | |
| | | place of | | - 27 | 0 | |
| | | conventional silicon substrates | | · / . | | 5 |
| | | in semiconductor | | | - | |
| | | manufacturing, especially | | | | |
| | | microelectronics, to | | | | |
| | | reduce parasitic device | | | 10 | |
| | | capacitance, thereby | | | | |
| | 1 | improving performance | | 6 | | |
| 15 | What is the | Latch up and body effect | Remember | CO 2 | CLO 5 | AEC017.05 |
| | significance of | issues are solved in this | | 1 | | |
| | SOI CMOS | technology by reducing | | | | |
| | technology? | parasitic capacitances. | | | | |
| 16 | What is voltage | Voltage droop is the | Remember | CO 2 | CLO 7 | AEC017.07 |
| | droop? | intentional loss in | | | | |
| | | output voltage from a device | | | | |
| | | as it drives a load. | | | | |
| 17 | What is ground | Ground bounce is usually seen | Remember | CO 2 | CLO 7 | AEC017.07 |
| | bounce? | on high density VLSI where | | | | |
| | | insufficient precautions have | | | | |
| | | been taken to supply a logic | | | | |
| | | gate with a sufficiently low | | | | |
| | | resistance connection (or | | | | |
| | | sufficiently high capacitance) | | | | |
| | | to ground. | | | | |
| 18 | Define noise | Noise margin is the amount | Understand | CO 2 | CLO 7 | AEC017.07 |
| | margin in | of noise that a CMOS | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
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| | CMOS circuit? | circuit could withstand | | | | |
| | | without compromising the | | | | |
| 10 | Dofino | Propagation delay is the | Domomhor | COD | CIO7 | AEC017.07 |
| 19 | propagation | difference in time (calculated | Kemember | 02 | CLO / | AEC017.07 |
| | delay | at 50% of input-output | | | | |
| | , | transition), when output | | | | |
| | | switches, after application of | | | | |
| 20 | | input. | | GO 0 | a a | |
| 20 | Define power | power consumption refers to | Remember | CO 2 | CLO 7 | AEC017.07 |
| | consumption | time | | | | |
| 21 | What are the | 1. Dynamic / Switching power | Remember | CO 2 | CLO 7 | AEC017.07 |
| | components of | 2. Static / leakage power | | - | | |
| | power | 3. Short circuit Power | | | | |
| 22 | What is PTL | Pass transistor logic describes | Understand | CO 2 | CLO 8 | AEC017.08 |
| | (Pass transistor | one of the several logic | | | | |
| | logic) ? | the count of transistors used to | | | | |
| | | make different logic gates, by | | | | |
| | | eliminating redundant | | | | |
| | | transistors. | | | | |
| 23 | What is the | ** ** | Understand | CO 2 | CLO 5 | AEC017.05 |
| | output voltage | $Vout = V_{DD} - V_T$ | | _ | | |
| | transistor logic) | | | | | |
| | device? | | | | | |
| 24 | How to | By using level restorer | Understand | CO 2 | CLO 5 | AEC017.05 |
| | overcome | transistors | | | | |
| | voltage drop in | | | | | |
| 25 | PTL device | Nagativa hias tamparatura | Domomhon | COL | CLO7 | AEC017.07 |
| 23 | CMOS? | instability (NBTI) is a key | Kemeniber | 02 | | AEC017.07 |
| | 0.1001 | reliability issue in MOSFETs. | | | | |
| | 0 | NBTI manifests as an increase | | -7 | C | |
| | 1 | in the threshold voltage and | | _ | - | |
| | ~ | consequent decrease in drain | | × . | A | |
| | 0 | and transconductance of a | | | | |
| | | MOSFET. The degradation is | | | 100 | |
| | · · · · · | often approximated by | | . 0 | | |
| | 1 | a power-law dependence on | · · · · | 67 | | |
| | | time. It is of immediate | | ~ | | |
| | | concern in p- | 111 | | | |
| | | (pMOS), since they almost | - | | | |
| | | always operate with negative | | | | |
| | | gate-to-source voltage; | | | | |
| | | however, the very same | | | | |
| | | mechanism also affects nMOS | | | | |
| | | accumulation regime i.e. with | | | | |
| | | a negative bias applied to the | | | | |
| | | gate. | | | | |
| 26 | What are the | Low Power | Understand | $CO\overline{2}$ | CLO 7 | AEC017.07 |
| | advantages of | Less Propagation delay | | | | |
| | PIL | LOW PDP Low FDP | | | | |
| 2.7 | What are | 1.Intrinsic gate canacitance | Remember | CO 2 | CLO 7 | AEC017 07 |
| | different | 2.overlap capacitance. | Remember | | | 1120017.07 |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-------------------|--|---------------------|----------|----------|-----------|
| | components in | | | | | |
| | gate | | | | | |
| | capacitance? | | | | | |
| 28 | Define diffusion | The parasitic capacitance arise | Remember | CO 2 | CLO 7 | AEC017.07 |
| | capacitance? | from reverse biased p-n | | | | |
| | | junction are called as diffusion | | | | |
| 20 | D C 10 | capacitance. | | 00.0 | CT 0 7 | |
| 29 | Define self- | Polysilicon with underlying | Remember | CO 2 | CLO 5 | AEC017.05 |
| | aligning? | thin oxide and the thick oxide | | | | |
| | | the process is self aligning | | | | |
| 30 | How latch up | Latch up problem can be | Pomombor | CO^{2} | CLO 5 | AEC017.05 |
| 50 | problem is | reduced by using a low- | Kemember | 02 | CLO J | AEC017.05 |
| | avoided? | resistivity epitaxial P- | | - | | |
| | uvolucu. | Substrate as the starting | | | | |
| | | material which act as very low | | \sim | | |
| | | resistance . | | | | |
| 31 | What is the | The function of this layer is to | Understand | CO 2 | CLO 5 | AEC017.05 |
| | purpose of the N | reduce the collector resistance | | | | |
| | buried layer? | of the transistor. | | | | |
| 32 | What is pull | A device connected so as to | Understand | CO 2 | CLO 8 | AEC017.08 |
| | down device? | pull the output voltage to the | | | | |
| | | lower supply voltage usually | | | | |
| | | 0V is called pull down device. | | | | |
| 33 | What is pull up | A device connected so as to | Remember | CO 2 | CLO 8 | AEC017.08 |
| | device? | pull the output voltage to the | | | | |
| | | VDD is called rull up device | | | | |
| 34 | Why NMOS | VDD is called pull up device. | Pomomhor | CO 2 | CLOS | AEC017.08 |
| 54 | technology is | greater switching speed when | Kemember | 02 | CLU 8 | AEC017.08 |
| | preferred more | compared the PMOS | | | | |
| | than PMOS | transistors. | | | | |
| | technology? | | | | | 1 |
| 35 | What are the | Cutoff region | Remember | CO 2 | CLO 5 | AEC017.05 |
| | different | Non- Saturated Region | | -7 | - C | |
| | operating | Saturated Region | | | | S |
| | regions foe an | | | 7 | 4 | |
| | MOS transistor | | | | | |
| 36 | Define Short | Transistors with Channel | Remember | CO 2 | CLO 8 | AEC017.08 |
| | Channel | length less than 3- 5 microns | | | | |
| | devices? | are termed as Short channel | | ~~ | | |
| | | devices. With short channel | - | 5 | | |
| | | lateral & vertical | | | | |
| | | dimensions are reduced | | | | |
| 37 | What are the | Low power Dissipation | Understand | CO 2 | CLO 7 | AEC017 07 |
| | advantages of | High Packing density | 2 actionality | 202 | | |
| | CMOS | Bi directional capability | | | | |
| | process? | | | | | |
| 38 | What are the | Additional masks defining P | Understand | CO 2 | CLO 5 | AEC017.05 |
| | basic processing | base region | | | | |
| | steps involved in | N Collector area Buried Sub | | | | |
| | Bi-CMOS | collector (SCCD) Processing | | | | |
| | process? | steps in CMOS process | | <i>a</i> | <u> </u> | |
| 39 | What are the | Tub Formation, Thin-oxide | Remember | CO 2 | CLO 5 | AEC017.05 |
| | steps involved in | Construction | | | | |
| | twin-tub | Contact out definition, | | | | |
| | process? | Matallization | | | | |
| | | | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-------------------|--|---------------------|--------|----------------|------------|
| 40 | What are the | No Latch-up, Due to absence | Remember | CO 2 | CLO 5 | AEC017.05 |
| | advantages of | of bulks transistor structures | | | | |
| | Silicon-on- | are denser than bulk silicon. | | | | |
| | Insulator | | | | | |
| | process? | | | | | |
| | | UNIT-III | | | | - |
| 1 | What are the | MOS circuits formed by four | Remember | CO 3 | CLO 10 | AEC017.10 |
| | basic layers of | basic layers n-diffusion, p- | | | | |
| | MOS circuits? | diffusion, polysilicon and | | | | |
| 2 | Define Chiele | metal. | D 1 | CO 2 | CLO 10 | AEC017.10 |
| 2 | Denne Stick | information through the use of | Remember | 005 | CLO 10 | AEC017.10 |
| | Diagram? | color code Also it is the | | | | |
| | | cartoon of a chip layout. | | - | | |
| 3 | What are the | It can be drawn much easier | Understand | CO 3 | CLO 10 | AEC017.10 |
| 5 | uses of Stick | and faster than a complex | Chaerstand | 000 | 02010 | 1120011110 |
| | diagram? | layout. These are especially | | | | |
| | ulagran | important tools for layout built | | | | |
| | | from large cells | | | | |
| 4 | Give the various | Green – n-diffusion . Red- | Remember | CO 3 | CLO 10 | AEC017.10 |
| | color coding | polysilicon, Blue –metal, | | | | |
| | used in stick | Yellow- implant, | | | | |
| | diagram? | Black-contact areas. | | | | |
| | ulagraill? | | | | | |
| 5 | What is the aim | Circuit designers in general | Understand | CO 3 | CLO 11 | AEC017.11 |
| 5 | of Circuit | prefer tighter, smaller layouts | onderstand | | | |
| | designers in IC | for improved performance and | | | | |
| | design? | decreased silicon area. | | | | |
| 6 | What is the aim | Process engineers wants | Understand | CO 3 | CLO 11 | AEC017.11 |
| - | of Process | design rules which are | | | | |
| | engineers with | controllable and reproducible | | | | |
| | respect to design | process. | | | | C |
| _ | rules? | | | | ST 0 11 | |
| 7 | What are | Design rules specify line | Understand | CO 3 | CLO 11 | AEC017.11 |
| | Lambda-based | widths, separations and | | 1 | - | |
| 8 | What is the | The width of n diffusion and | Understand | CO 3 | CLO 11 | AEC017 11 |
| 0 | width and | p -diffusion should be 2 λ the | onderstallu | 003 | | ALC01/.11 |
| | spacing between | spacing between two diffusion | | | | |
| | two diffusion | layers should be 3λ according | | 28 | 1. C | |
| | layers? | to design rules. | | Sec. 1 | | |
| 9 | What is the layer | Each and every layer is | Understand | CO 3 | CLO 10 | AEC017.10 |
| | used to separate | isolated by thick or thin silicon | | | | |
| | each transistor | dioxide insulating layers. | | | | |
| | layer? | | | | | |
| 10 | Define Butting | The gate and source of a | Remember | CO 3 | CLO 10 | AEC017.10 |
| | contacts | depletion device can be | | | | |
| | | connected by a method known | | | | |
| | | as butting contact. Here metal | | | | |
| | | diffusion forming the source of | | | | |
| | | the depletion transistor and to | | | | |
| | | the poly silicon forming this | | | | |
| | | device's gate. | | | | |
| 11 | What is the | The width of the metal 1 laver | Understand | CO 3 | CLO 11 | AEC017.11 |
| | width and | should be 3λ and metal 2 | | | | |
| | spacing between | should be 4λ , spacing between | | | | |
| | two metal | two metal 1 layers should be | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|----------|-------------------|------------------------------------|---------------------|------|----------------|-------------|
| | layers? | 3λ and spacing between two | | | | |
| | | metal 2 should be 4λ , | | | | |
| 12 | What is the | Implant for a n-mos depletion | Remember | CO 3 | CLO 11 | AEC017.11 |
| | implant | minimum of 2λ from the | | | | |
| | implant | channel in all the directions. | | | | |
| 13 | Which type of | Buried contacts are much | Understand | CO 3 | CLO 11 | AEC017.11 |
| | contact cuts is | better than butted contacts. | | | | |
| | better? | In butted contacts the two | | | | |
| | | hinded together using | | | | |
| | | adhesive type of material | | | | |
| | | where as in buried contact | | | | |
| | | one layer is interconnected | | | | |
| | | or fitted into another. | D 1 | 00.2 | GT 0 11 | AEC017.11 |
| 14 | Contacts | The buried contact is a method | Remember | 03 | CLO II | AEC017.11 |
| | contacts | to make direct onmic contact | | | | |
| | | material and the junctions in | | | | |
| | | silicon-gate integrated circuits | | | | |
| | | sincon-gate integrated circuits. | | | | |
| 15 | Define hard | It means permanent functional | Remember | CO 3 | CLO 13 | AEC017.13 |
| | failures in | failures of the chip | | | | |
| | curve? | | | | | |
| 16 | Which is more | Butting contact is complex | Understand | CO 3 | CLO 11 | AEC017.11 |
| | complex process | process whereas buried contact | | | | |
| | in butting? | is simple process because | | | | |
| | | butting contact should be done | | | | |
| | | and be strong. | | | | |
| 17 | Define | Transient failures can come bit | Remember | CO 3 | CLO 13 | AEC017.13 |
| | transient | flips and timing errors. | | - 17 | | 0 |
| | failures? | | | 00.0 | AT 0 10 | 4.5.0017.10 |
| 18 | Which layer is | Metal layers are used for | Remember | CO 3 | CLO 10 | AEC017.10 |
| | and signal lines? | metals has good thermal and | | 7 | 1 | |
| | U | electrical conductivity. | | | (| |
| 19 | What is the | The minimum width of n-well | Remember | CO 3 | CLO 11 | AEC017.11 |
| | Minimum n-well | is 3 micro meter because n- | | - 0 | 1 C C | |
| | width should be | thickness and in it p-type | | 67 | 84 | |
| | in mero meter : | devices are formed. | 0 | ~ | | |
| 20 | What is the | The minimum spacing | Remember | CO 3 | CLO 11 | AEC017.11 |
| | Minimum | between two n-well is 8.5 | 1 | | | |
| | spacing between | micro meter according to the | | | | |
| 21 | What are the | Design rules are those are | Understand | CO 3 | CLO 11 | AFC017 11 |
| <u> </u> | advantages of | durable, scalable, portable, | Understalld | 203 | | |
| | design rules? | increases designer efficiency | | | | |
| | | and automatic translation to | | | | |
| - 22 | Which color | final layout can be done. | TT. 1 | CO 2 | CL O 10 | AEC017 10 |
| | is used for | polysilicon layers. Orange | Understand | 05 | | AEC017.10 |
| | polysilicon,p | color is used to represent | | | | |
| | olysilicon2? | polysilicon-2 layer | | | | |
| 23 | Define | Defect that occurs due to | Remember | CO 3 | CLO 13 | AEC017.13 |
| | metallization | Scratches and voids, | | | | |
| L | iuiiuie | meenumeur uumuge, non- | | | l | 1 |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|---------------------------------|------------------------------------|---------------------|-------------|---------|-----------|
| | mechanism | ohmic contacts, step coverage, | | | | |
| | | weak adhesion, improper | | | | |
| | | thickness, corrosion, | | | | |
| | | migration stress | | | | |
| 24 | How to represent | Implant is represented using | Remember | CO 3 | CLO 11 | AEC017.11 |
| | implant? | yellow color dotted lines. It is | | | | |
| | | drawn in the middle of the | | | | |
| | | nMOS or pMOS where ever | | | | |
| | | the implant is used. | | GO 0 | GL 0.10 | |
| 25 | Define electrical | When two or more sticks | Remember | CO 3 | CLO 10 | AEC017.10 |
| | diagram? | touch each other then that | | | | |
| | diagram. | forms a contact called | - | - | | |
| | ~ | electrical contact. | | | | |
| 26 | What is the | Interconnect increases circuit | Remember | CO 3 | CLO 12 | AEC017.12 |
| | effect of | delay for two reasons. First, | | | _ | |
| | Interconnect on | the wire capacitance adds | | | | |
| | MOS devices ? | loading to each gate. Second, | | | | |
| | | long wires have significant | | | | |
| | | distributed RC delay or flight | | | | |
| | | time, wire delay grows | | | | |
| | | quadratically with length. | | | | |
| 27 | Define crosstalk | wires have | Understand | CO 3 | CLO 12 | AEC017.12 |
| | effect of wir <mark>es</mark> ? | capacitance to their | | | | |
| | | adjacent neighbors as | | | | |
| | | well as to ground. | | | | |
| | | when wire A | | | | |
| | | switches, it tends to | | | | |
| | | bring its neighbor B | | | | |
| | 5 | along with it on | | | | 100 |
| | | account of | | | | - |
| | 0 | capacitive coupling, | | -7 | - C | |
| | D.C. I.C. | also called <i>crosstalk</i> . | - | 00.0 | GY 0 10 | 15001510 |
| 28 | Define infant | Chip failures that are caused | Remember | CO 3 | CL0 13 | AEC017.13 |
| | monanty? | by a variety of fabrication | | | | |
| | | flaws that create marginal | | 1.1 | 100 | |
| | · · · · · | structures such as thin wires or | | 0 | | |
| | | malformed transistors. | | 67 | | |
| 20 | Define | This metric defines the mean | 0 | CO 3 | | AEC017 13 |
| 29 | mean time | time to the next occurrence of | Remember | 05 | CLO 13 | ALC017.15 |
| | to failure | a given failure mechanism. | 1 | | | |
| | (MTTF). | Based on MTTF, we can | | | | |
| | | determine other interesting | | | | |
| | | metrics, such as lifetime . | | | | |
| 30 | Define diffusion | Crystal defects, impurity | Remember | CO 3 | CLO 13 | AEC017.12 |
| | and junctions | precipitation, mask | | | | |
| | | misalignment, surface | | | | |
| | | contamination. | | | | |
| 21 | Define | Failure that occurs due to | | CO^{3} | | AEC017 12 |
| 51 | passivation | Pinholes and cracks thickness | Understand | 005 | CLO 13 | ALC017.13 |
| | failure ? | variations, contamination. | | | | |
| | | surface inversion | | | | |
| 32 | Define Time- | TDDB Time-dependent | Understand | CO 3 | CI O 13 | AEC017.13 |
| | dependent | dielectric breakdown | Understallu | | CLU 15 | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|------------------------------|-----------------------------------|---------------------|------|--------------|--------------|
| | dielectric | occurs because the electric | | | | |
| | breakdown | fields across gate oxides | | | | |
| | | induce stresses that | | | | |
| | | damage the oxide. | | | | |
| 33 | Define hot | It is a carrier that gains enough | Remember | CO 3 | CLO 13 | AEC017.13 |
| | carrier | energy to jump from the | | | | |
| | | silicon substrate into the gate | | | | |
| | | oxide. As these hot carriers | | | | |
| | | accumulate, they create a | | | | |
| | | space charge in the oxide that | | | | |
| | | affects the transistor's | | | | |
| | | neremeters | | | | |
| 24 | Dofino Nogotivo | f_{a} | | CO 3 | CL 0 13 | AEC017 13 |
| 54 | bias temperature | pMOS devices due to stress | Remember | 05 | CLU 15 | AEC017.15 |
| | instability | that introduces interface states | | | | |
| | mstability | and space charge | | | | |
| 35 | Define failu <mark>re</mark> | It is due to Mobile ions | Remember | CO 3 | CLO 13 | AEC017 13 |
| 55 | mechanism | pinholes, interface states, hot | remember | 005 | | 11120017.113 |
| | occurs in | carriers, time dependent | | | | |
| | oxides? | dielectric breakdown. | | | | |
| 36 | Define | Electrons drifting through the | Understand | CO 3 | CLO 13 | AEC017.13 |
| | Electromigration | voltage gradient on a metal | | | | |
| | | line collide with the metal | | | | |
| | | grains. Under high currents, | | | | |
| | | electron collisions with metal | | | | |
| | | grains cause the metal to | | | | |
| | | move; this process is called | | | | |
| | | metal migration (also known | | | | |
| 27 | D | as electromigration). | D | 00.2 | CL 0 12 | AEC017.12 |
| 57 | Define stress | Stress migration is caused by | Remember | 0.03 | CLO IS | AEC017.15 |
| | Inigration | occur even when no current | | | | |
| | C | flows through the wire These | | | | C |
| | 0 | stresses are caused by the | | | | |
| | | different thermal expansion | | | · · · · | e |
| | 6 | coefficients of the wires and | | | ~ | |
| | | the materials in which they | | | · · · · | |
| | 0 | reside | | | | |
| 38 | Define soft | Soft errors cause memory cells | Understand | CO 3 | CLO 13 | AEC017.13 |
| | errors in VLSI | to change state. Soft errors can | | | S | |
| | | be caused by alpha particles | | 6.7 | | |
| | | that generate excess carriers as | | ~ | | |
| | | they travel through the | | | | |
| 20 | Define Latel and | substrate. | Demousher | CO 2 | $CI \cap 12$ | AEC017.12 |
| 39 | in CMOS 2 | Laten-up is a condition in | Remember | 0.5 | CLO 15 | AEC017.15 |
| | | components give rise to the | | | | |
| | | establishment of low | | | | |
| | | resistance conducting paths | | | | |
| | | between V_{DD} and V_{sc} | | | | |
| 40 | Define via | It is the contact between metal | Remember | CO 3 | CLO 11 | AEC017.11 |
| | contact? | 1 and metal 2. | | | | |
| | | UNIT-IV | 7 | | | |
| 1 | What is static | Static CMOS logic is a | Remember | CO 4 | CLO 19 | AEC017.19 |
| | CMOS logic? | combination of two networks | | | | |
| | | ,Pull up Network using PMOS | | | | |
| | | transistors and Pull down | | | | |
| | | network using NMOS | | | | |
| | | transistors. They are dual with | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|--------------------------|--|---------------------|------|----------------|------------|
| | | each other.At any time ,any | | | | |
| | | one of the network is on | | ~~ (| CT 0 10 | |
| 2 | What is dynamic | Dynamic circuits reduce the | Understand | CO 4 | CLO 19 | AEC017.19 |
| | CMOS logic? | drawbacks of ratioed circuits | | | | |
| | | using a clock input to the pull | | | | |
| | | requires N+2 transistors and | | | | |
| | | there are two modes of | | | | |
| | | operation ,Pre-charge and | | | | |
| | | Evaluation | | | | |
| 3 | What are the | •Consume significant | Remember | CO 4 | CLO 19 | AEC017.19 |
| | disadvantages of | dynamic power | | | | |
| | dynamic logic? | •Sensitive to noise during | | | | |
| | | evaluation | | | | |
| | C | Carefull clocking | | | | |
| | | Monotonicity problem | | | | |
| 4 | Why domin <mark>o</mark> | In dynamic logic ,there is | Understand | CO 4 | CLO 19 | AEC017.19 |
| | logic is preferred | cascading problem. This | | | | |
| | over dynamic | can be solved by placing a | | | | |
| | logic? | static – CMOS inverter | | | | |
| | | between dynamic gates. | | | | |
| | | together is called domino | | | | |
| | | logic | | | | |
| 5 | Define | The propagation delay | Remember | CO 4 | CLO 15 | AEC017.15 |
| | propagation | is the time taken to | | | | |
| | delay | change the output after | | | | |
| | | applying the input. This | | | | |
| | | is the upper bound on | | | | |
| | | interval between valid | | | | |
| | | inputs and valid | | | | |
| 6 | What is the | Static dissipation is due to sub | Understand | CO 4 | CL O 19 | AEC017 19 |
| 0 | cause of static | threshold conduction through | Onderstand | 004 | CLO I) | ALCOITI |
| | power | off transistor. | | | | |
| | dissipation? | Constitution of the second second | | | ~ | |
| 7 | State any two | The low power can be | Remember | CO 4 | CLO 21 | AEC017.21 |
| | criteria for low | achieved by lowering the | 1 | | - C | |
| | power logic | effective capacitance. The non | | | 100 | |
| | design | active modules can be made to | | 28 | h | |
| | 1 | stand by mode to reduce the | | S. 1 | | |
| 8 | What is | Transmission gate is | Understand | CO 4 | CLO 14 | AEC017 14 |
| 0 | transmission | constructed by combining an | Chaerstand | 004 | | 71LC017.14 |
| | gate? | NMOS transistor and PMOS | - | | | |
| | 0 | transistor in parallel. It acts as | | | | |
| | | a switch that turns on when a | | | | |
| | | '1' is applied to the gate 'A'. | | | | |
| | | When A=1,'0'and '1'can be | | | | |
| 0 | What is pass | This type of last | Domomhan | CO 4 | | AEC017 14 |
| 9 | transistor logic? | NMOS transistors alone In | Remember | CO 4 | CLO 14 | AEC017.14 |
| | transistor logic: | this gate is driven by a | | | | |
| | | control signal .the source (out | | | | |
| | |), the drain of the transistor is | | | | |
| | | called constant or variable | | | | |
| | | voltage potential (in) when the | | | | |
| | | control signal is high, the | | | | |
| | | input is passed to the output | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-------------------|----------------------------------|---------------------|-------------|----------------|------------|
| | | and when the control signal is | | | | |
| | | low, the output is floating | | | | |
| | | such topology circuit is called | | | | |
| | | pass transistor. | | ~~ (| ~ ~ ~ ~ | |
| 10 | Why single | In cascading problem arises | Understand | CO 4 | CLO 19 | AEC017.19 |
| | phase dynamic | because the output of each gate | | | | |
| | logic structure | are pre-charged to 1 and due | | | | |
| | cannot be | to this some charge will be | | | | |
| | Lustify | loss and leads to reduced noise | | | | |
| | Justify | margin and potential | | | | |
| | | malfunctioning | | | | |
| 11 | Write the design | Standard cell design | Remember | CO 4 | CLO 17 | AEC017.17 |
| | style | Gate array design : | - | - | | |
| | classification of | Channelled Gate Array | | | | |
| | Semi custom | Channel less Gate | | | | |
| | design ASICs | Array | | | | |
| 12 | Write the design | PLDs, FPGA | Understand | CO 4 | CLO 17 | AEC017.17 |
| | style | | | | | |
| | classification of | | | | | |
| | Programmable | | | | | |
| 12 | ASICs | | Dent | CO 4 | CI O 17 | AEC017.17 |
| 15 | types of A SICs? | Semi custom ASICs | Remember | CO 4 | | AEC017.17 |
| 14 | What are the | Programming Techniques of | Understand | CO 4 | CL 0 17 | AFC017 17 |
| 14 | different types | PAL are | Onderstand | 004 | | ALCOIV.IV |
| | of programming | 1. Fusible Links | | | | |
| | structure | programming | | | | |
| | available in | 2. UV-Erasable | | | | |
| | PAL? | EPROM | | | | |
| | | programming | | | | |
| | | 3. EEPROM | | | | |
| | 0 | programming | | | | 100 |
| 15 | What are the | All mask layers are | Remember | CO 4 | CLO 17 | AEC017.17 |
| | features of | customized- transistors and | | _ | | 2 |
| | A SICo2 | hlocks can be embedded | | - C | | |
| | ASICS? | Manufacturing lead time is | | × . | A | |
| | 0 | about eight weeks | | | | |
| 16 | Define Total | It is defined as the sum of area | Understand | CO 4 | CLO 15 | AEC017 15 |
| 10 | wire | capacitance and fringing field | Chaeistana | 001 | CLO IS | 1112011115 |
| | capacitance? | capacitance. | | 27 | | |
| 17 | How the | Interlayer capacitance occurs | Understand | CO 4 | CLO 15 | AEC017.15 |
| | Interlayer | due to parallel plate effect | | 1 | | |
| | capacitance | between one layer and | | | | |
| | occurs | another. When one | | | | |
| | | capacitance value comes | | | | |
| | | closer to another they create | | | | |
| 10 | *** | some combined effects. | | GO 4 | GY 0 15 | |
| 18 | What are the | • None of the mask | Remember | CO 4 | CLO I7 | AEC017.17 |
| | EDC A 2 | layers are | | | | |
| | TTUA! | customized. | | | | |
| | | • .A method for | | | | |
| | | basic logic cells and | | | | |
| | | the interconnect | | | | |
| | | • This is used to | | | | |
| | | implement | | | | |
| | | combinational as | | | | |
| | | well as sequential | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-----------------------|--|---------------------|--------|-----------------|-----------|
| | | logic (flip-flops). | | | | |
| 19 | What is | A programmable logic array | Understand | CO 4 | CLO 17 | AEC017.17 |
| | programmable | (PLA) is a programmable | | | | |
| | logic array? | device used to implement | | | | |
| | | combinational logic circuits. | | | | |
| | | The PLA has a set of | | | | |
| | | programmable AND planes, | | | | |
| | | which link to a set of | | | | |
| 20 | What is mean by | The Programmable logic planes. | Domomhor | CO 4 | CLO 17 | AEC017.17 |
| 20 | Programmable | is programmable read only | Remember | CO 4 | CLU I/ | AEC017.17 |
| | logic plane? | memory (PROM) array that | | | | |
| | logie plane. | allows the signals present on | | | | |
| | | the devices pins (or the | | | | |
| | - | logical components of those | | | | |
| | | signals) to be routed to an | | \sim | | |
| | | output logic macro cell | | | | |
| 21 | How the switch | Switch logic is designed using | Understand | CO 4 | CLO 14 | AEC017.14 |
| | logic is | n or p pass transistors or from | | | | |
| | designed? | complementary switches. | | | | |
| 22 | List the steps in | Design entry. Enter the design | Understand | CO 4 | CLO 17 | AEC017.17 |
| | ASIC design | into an ASIC design system, | | | | |
| | flow | either using a hardware | | | | |
| | | description language (HDL) or | | | | |
| | | schematic entry. | | | | |
| | | Logic synthesis. Use an HDL | | | | |
| | | (VHDL or Verilog) and a logic | | | | |
| | | synthesis tool to produce a net | | | | |
| 23 | Dofino Fall time | $\begin{array}{c} \text{IISL} \\ \text{Fall time } \tau f \text{ is the time taken} \end{array}$ | Pamamhar | CO 4 | CLO 15 | AEC017 15 |
| 23 | Denne Pan unie | for a waveform to fall from | Kemember | 04 | CLO 15 | ALC017.15 |
| | | 90% to 10% of its steady state | | | | |
| | | value. | | | | 100 |
| 24 | Define Delay | Delay time, τd is the time | Understand | CO 4 | CLO 15 | AEC017.15 |
| | time | difference between input | | | - C | |
| | 1 | transition (50%) and the | | | | |
| | 0 | 50% output level. This is the | | | | |
| | 0 | time taken for a logic | | | | |
| | | transition to pass from input to | | | Sec. 1 | |
| | | output. | | ~~ · · | AT A 4 A | |
| 25 | What are two | These are: | Remember | CO 4 | CLO 19 | AEC017.19 |
| | components of | 1) Static dissipation due to | - | Sec. 1 | | |
| | power dissinction? | leakage current or other | | | | |
| | uissipation? | from the power supply | | | | |
| | | ii) Dynamic dissination due to | | | | |
| | | - Switching transient current - | | | | |
| | | Charging and discharging of | | | | |
| | | load capacitances. | | | | |
| 26 | What is the full | In a full custom ASIC, an | Understand | CO 4 | CLO 17 | AEC017.17 |
| | custom ASIC | engineer designs some or all of | | | | |
| | design? | the logic cells, circuits or | | | | |
| | | layout specifically for one | | | | |
| L | | ASIC. | | | | |
| 27 | What is the | A cell-based ASIC (CBIC) | Understand | CO 4 | CLO 17 | AEC017.1 |
| | standard cell- | uses predesigned logic cells | | | | |
| | dosign? | ASIC designer defines or la | | | | |
| | uesign: | the placement of standard calls | | | | |
| | | and the interconnect in a | | | | |
| L | I | and the interconnect in a | 1 | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-------------------|-----------------------------------|---------------------|------------------|---------|------------|
| | | CBIC. All the mask layers of a | | | | |
| | | CBIC are customized and are | | | | |
| | | unique to a particular | | | | |
| 29 | Differentiate | customer. | I lu de note u d | <u> </u> | CL 0 17 | AEC017 17 |
| 28 | batwaan | In Channeled Gate Array only | Understand | CO 4 | CL0 17 | AEC017.17 |
| | channeled & | but in channelless Gate Array | | | | |
| | channel less gate | only the top few mask layers | | | | |
| | array. | customized. | | | | |
| 29 | Give the | 2V10 I/O cell consists of a | Remember | CO 4 | CLO 17 | AEC017.17 |
| | constituent of | register ,output 4:1 mux, a tri- | | | | |
| | I/O cell in | state buffer,a 2:1 input mux. | | | | |
| | 22V10. | | | | | |
| 30 | What are the | The programming of PALs is | Understand | CO 4 | CLO 17 | AEC017.17 |
| | different | done in three main | | <u> </u> | | |
| | programming of | ways: • Fusible links • $UV =$ | | | | |
| | PALs? | • EEPROM (E2PROM) - | | | | |
| | 111113. | Electrically Erasable | | | | |
| | | Programmable ROM | | | | |
| 31 | What are | In a PAL, the device is | Understand | CO 4 | CLO 17 | AEC017.17 |
| | Programmable | programmed by changing the | | | | |
| | Interconnects ? | characteristics if the | | | | |
| | | switching element. An | | | | |
| | | alternative would be to | | | | |
| 32 | What is the | The switch logic approach | Understand | CO 4 | CLO 14 | AEC017 14 |
| 32 | advantage of | takes no static current from the | Understand | CU 4 | CLO 14 | AEC017.14 |
| | switch logic? | supply rails and is faster for | | | | |
| | switch logie. | small arrays. | | | | |
| 33 | Define Gate | Gate logic is also called as | Understand | CO 4 | CLO 14 | AEC017.14 |
| | logic? | restoring logic. This is a logic | | | | |
| | 5 | circuitry designed so that even | | | | - |
| | - | with an imperfect input pulse a | | | | |
| | | standard output occurs at the | | - | - C | 2 |
| | 6 | exit of each successive logic | | | | |
| 34 | What is the pull | For a pseudo nMOS design | Understand | CO 4 | CLO 14 | AFC017 14 |
| 51 | up and pull | the ratio of Zp.u. and Zp.d. is | Childerstand | 001 | CLO II | ALLCOI / |
| | down impedance | 3:1. | | | 100 | |
| | ratio is pseudo | | | Q | S | |
| | nMOS design ? | 1 | | 62 | | |
| 35 | In which region | In Pseudo-nMOS logic, n | Understand | CO 4 | CLO 14 | AEC017.14 |
| | Pseudo-nMOS | transistor operates in saturation | | | | |
| | logic operates? | region and p transistor | | | | |
| 36 | What are the | Some of the features of switch | Understand | CO 4 | CL O 14 | AFC017 14 |
| 50 | features of | logic approach are that it | Childerstand | 004 | CL0 14 | 7120017.14 |
| | switch logic | occupies more area, eliminates | | | | |
| | approach | undesirable threshold voltage | | | | |
| | - | and has low power dissipation. | | | | |
| 37 | Which | The sources of capacitances | Remember | $CO\overline{4}$ | CLO 15 | AEC017.15 |
| | contribute to the | which contribute to the total | | | | |
| | wiring | wiring capacitance are fringing | | | | |
| | capacitance? | neid capacitance, interlayer | | | | |
| | | capacitance and peripheral | | | | |
| 38 | Which | Metal to polysilicon | Remember | CO 4 | CLO 15 | AEC017 15 |
| 50 | capacitance must | capacitance should be higher | | CO T | | |
| | be higher? | than metal to substrate | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|-------|-----------------|----------------------------------|---------------------|--|----------------|------------|
| | | capacitance. This is due to that | | | | |
| | | when one layer underlies the | | | | |
| | | other and inconsequence | | | | |
| | | dependent on layout | | | | |
| UNIT. | -V | dependent on layout. | | | | |
| 1 | What is | A parallel adder is an | Remember | CO5 | CLO 19 | AEC017.19 |
| | parallel adder? | arithmetic combinational | | | | |
| | - | logic circuit that is used to | | | | |
| | | add more than one bit of data | | | | |
| | XX 71 | simultaneously. | TT 1 1 | 005 | CT 0 10 | 45001510 |
| 2 | What is | The memory cell is an | Understand | 005 | CLO 19 | AEC017.19 |
| | memory cen? | one bit of binary information | | - | | |
| | - | and it must be set to store a | 1.1 | | | |
| | | logic 1 (high voltage level) | | \sim | | |
| | | and reset to store a logic 0 | | | | |
| | | (low voltage level). Its value | | | | |
| | | is maintained/stored until it is | | | | |
| | | changed by the set/reset | | | | |
| 3 | What is ROM? | ROM is a type of memory | Remember | CO5 | CLO 19 | AEC017 19 |
| 5 | | that normally can only be | remember | 005 | | 7112017.17 |
| | | read, as opposed to RAM | | | | |
| | | which can be both read and | | | | |
| | | written | | <i><i>a</i> a</i> <i>a</i> | ST 0 10 | |
| 4 | What is | This is a type of ROM that | Understand | CO5 | CLO 19 | AEC017.19 |
| | PROM? | can be programmed using | | | | |
| | | written to but only once | | | | |
| 5 | What is | An asynchronous DRAM | Remember | CO5 | CLO 19 | AEC017.19 |
| | Synchronous | chip has power connections, | | | | |
| | DRAM? | some number of address | | _ | | |
| | - | inputs (typically 12), and a | | | | |
| | | few (typically one or four) | | - | | 2 |
| 6 | What is | An asynchronous DRAM | Remember | C05 | CLO 20 | AFC017 20 |
| 0 | Synchronous | chip has power connections. | Remember | 005 | CLO 20 | 71LC017.20 |
| | DRAM? | some number of address | | | - · · · | |
| | -2 | inputs (typically 12), and a | | ~ | | |
| | | few (typically one or four) | | 28 | | |
| | W/h at is set | bidirectional data lines. | I Indonetica 1 | COF | | AEC017.21 |
| / | what is meant | adder that is capable of | Understand | COS | CLU 21 | AEC017.21 |
| | adder? | adding two 4-hit words | 1 1 1 1 | | | |
| | | having a BCD (binary-coded | · · · · · · | | | |
| | | decimal) format | | | | |
| 8 | Where is BCD | Binary-coded Decimal or | Remember | CO5 | CLO 21 | AEC017.21 |
| | used? | BCD is a way of representing | | | | |
| | | a decimal number as a string | | | | |
| | | electronic systems | | | | |
| 9 | What is a 4 bit | a combinational circuit which | Remember | CO5 | CLO 21 | AEC017 21 |
| Í | parallel adder? | is used to add two N-bit | | 2.55 | 22021 | |
| | · · · · · · | binary numbers | | | | |
| 10 | What is a in | A binary code represents | Understand | CO5 | CLO 21 | AEC017.21 |
| | binary code? | text, computer processor | | | | |
| | | instructions, or any other data | | | | |
| | | using a two-symbol system. | | | | |
| | | | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|-----------------|---------------------------------|---------------------|-----|---------|-------------|
| 11 | What is fast | A carry-lookahead adder | Remember | CO5 | CLO 20 | AEC017.20 |
| | adder? | (CLA) or fast adder is a type | | | | |
| | | of adder used in digital logic. | | | | |
| 12 | What are | A Universal shift register is a | Understand | CO5 | CLO 20 | AEC017.20 |
| | universal shift | register which has both the | Charistand | 000 | 020 20 | 11120017120 |
| | registers? | right shift and left | | | | |
| | registers. | shift with parallel load | | | | |
| | | canabilities Universal shift | | | | |
| | | registers are used as memory | | | | |
| | | elements in computers | | | | |
| 13 | What is the | Both shift registers and | Understand | CO5 | CLO 20 | AFC017 20 |
| 15 | difference | counters are made of flin- | Onderstand | 005 | CLO 20 | 71LC017.20 |
| | between | flops A shift register is | | | | |
| | register and | simply a chain of EEs where | | | | |
| | shift register? | the O output of one EE | | | | |
| | shift register: | connects to the D input of the | | | | |
| | | post A shift register will | | | | |
| | | transfer data from one FE to | | | | |
| | | the next on each clock event | | | | |
| 14 | What is a | A dynamic shift register | Remember | COS | CL O 20 | AEC017.20 |
| 14 | dynamic shift | circuit comprises an input | Kemember | 005 | | ALCOI7.20 |
| | rogistor? | terminal and an output | | | | |
| | register ! | terminal The logic circuit is | | | | |
| | | made operative by an output | | | | |
| | | signal of the signal follower | | | | |
| | | signal of the signal follower | | | | |
| | | inverter function at the output | | | | |
| | | terminal in response to an | | | | |
| | | output signal of the second | | | | |
| | | transfer gate circuit | | | | |
| 15 | Dofino | Sequential circuit has | Understand | COS | CLO 21 | AEC017 21 |
| 15 | Sequential | memory as output can yerry | Understand | COS | CL0 21 | AEC017.21 |
| | sequential | has d on input. This type of | | | | |
| | circuits. | sirguita usos provious input | | | | C |
| | | output clock and a mamory | | | | |
| | | element | | | - N | 2 |
| 16 | What is | An EPROM is a ROM that | Remember | COS | CLO 21 | AEC017 21 |
| 10 | FPROM? | can be erased and | Kememoer | 005 | CLO 21 | ALC017.21 |
| | | reprogrammed | | | | |
| 17 | What is | Electrically Eroschle | Understand | COS | CL O 22 | AEC017 22 |
| 17 | What is | Programmable POM | Understand | COS | CLO 22 | AEC017.22 |
| 10 | EEF KOWI : | Programmia rendem eccess | Domombon | COS | CLO 22 | AEC017.22 |
| 10 | DRAM9 | memory | Kemember | COS | CLU 22 | AEC017.22 |
| 10 | DIAM: | A decoder is a aircuit that | Domomhor | C05 | CLO 22 | AEC017 22 |
| 19 | decodor | changes a code into a set of | Kemennber | COS | CLU 22 | AEC017.22 |
| | uecouer. | signals. It is called a decoder | | | | |
| | | because it does the reverse of | | | | |
| | | anading but we will begin | | | | |
| | | our study of oncoders and | | | | |
| | | doordars with doordars | | | | |
| | | because they are simpler to | | | | |
| | | design | | | | |
| 20 | Dofina an | The poutput lines second | Underster 1 | COF | CLO 21 | AEC017.21 |
| 20 | Denne an | the binery code for the | Understand | 005 | CLU 21 | AEC017.21 |
| | encouer. | ne officiary code for the | | | | |
| | | possible 2n input lines. Let us | | | | |
| | | take an example of an octal- | | | | |
| 1 | Define mit | Dinomy Error Jam | Und-ante 1 | COF | CLO 21 | AEC017.21 |
| 21 | Define priority | binary Encoders generally | Understand | CUS | CLU 21 | AEC017.21 |
| | encoder. | nave a number of inputs that | | | | |
| 1 | | must be mutually exclusive, | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|----------------|--|---------------------|--------------|----------------|-------------|
| | - | i.e. only one of the inputs can | | | | |
| | | be active at any one time. | | | | |
| | | The encoder then produces a | | | | |
| | | binary code on the output | | | | |
| | | pins, which changes in | | | | |
| | | response to the input that has | | | | |
| | D.C. 1.10 | been activated. | XX 1 1 | 005 | GL 0.01 | 1001201 |
| 22 | Define half | Half adder is a combinational | Understand | CO5 | CLO 21 | AEC017.21 |
| | adder. | circuit, which performs the | | | | |
| | | addition of two binary | | | | |
| | | single bit. It produces two | | | | |
| | | outputs sum S & carry C | | | | |
| 23 | What is binary | The most basic arithmetic | Understand | COS | CL O 19 | AEC017 19 |
| 25 | adder? | operation is addition The | Onderstand | 005 | CLO I) | ALCOIT.IT |
| | adder . | circuit which performs the | | | | |
| | | addition of two binary | | | | |
| | | numbers, is known as Binary | | | | |
| | | adder. | | | | |
| 24 | Define full | Full adder is a combinational | Understand | CO5 | CLO 19 | AEC017.19 |
| | adder. | circuit, which performs the | | | | |
| | | addition of three | | | | |
| | | bits A, B and Cin. Where, A | | | | |
| | | & B are the two parallel | | | | |
| | | significant bits and Cin is the | | | | |
| | | carry bit, which is generated | | | | |
| | | from previous stage. | | | | |
| 25 | Define | Multiplexer is a | Understand | CO5 | CLO 19 | AEC017.19 |
| | multiplexer. | combinational circuit that has | | | | |
| | | maximum of 2 ⁿ data inputs, | | | | |
| | | 'n' selection lines and single | | | | |
| | | output line. One of these data | | | | |
| | | inputs will be connected to | | | | C |
| | | the output based on the | | | | |
| | | values of selection lines. | | | CT C 10 | |
| 26 | Define | De-Multiplexer is a | Remember | CO5 | CLO 19 | AEC017.19 |
| | Demultiplexer | combinational circuit that | | | ~ | |
| | | performs the reverse | | | | |
| | | bas single input 'n' selection | | | 10 | |
| | | has single input, it selection | | _ Q | S | |
| | | lines and maximum of 2" | | 0.7 | | |
| | | outputs. The input will be | 0 | ~ | | |
| | | connected to one of these | | | | |
| | | of selection lines | | | | |
| 27 | Define | Digital Comparator A | Remember | COS | CLO 20 | AEC017.20 |
| 27 | comparator | magnitude digital comparator | Remember | 005 | CLO 20 | 71120017.20 |
| | computation. | is a combinational circuit that | | | | |
| | | compares two digital or | | | | |
| | | binary numbers (consider A | | | | |
| | | and B) and determines their | | | | |
| | | relative magnitudes in order | | | | |
| | | to find out whether one | | | | |
| | | number is equal, less than or | | | | |
| | | greater than the other digital | | | | |
| | | number. | | <i>a</i> : - | | |
| 28 | What is code | Codes and code converters | Understand | CO5 | CLO 21 | AEC017.21 |
| | converter? | Coding is the process of | | | | |
| | | translating the input | | | | |

| S.No | QUESTION | ANSWER | Blooms Level | CO | CLO | CLO Code |
|------|------------------------------------|--|---------------------|-----|--------|-----------|
| | | information which can be understandable by the machine or a particular device. Coding can be used for security purpose to protect the information from steeling or interrupting. | | | | |
| 29 | What is parallel adder? | A parallel adder is an arithmetic combinational logic circuit that is used to add more than one bit of data simultaneously. | Remember | CO5 | CLO 21 | AEC017.21 |
| 30 | What is one- to-one mapping? | each input code word produces a different output code word | Remember | CO5 | CLO 21 | AEC017.21 |
| 31 | What is binary decoder? | has an n-bit binary input code and a 1-out-of-2n output code | Understand | CO5 | CLO 22 | AEC017.22 |
| 32 | What is binary encoder? | If the device's output code has fewer bits than the input code, the device is usually called an encoder | Remember | CO5 | CLO 22 | AEC017.22 |
| 33 | What is multiplexer? | a digital switch—it connects data from one of n sources to its output | Remember | CO5 | CLO 22 | AEC017.22 |
| 34 | What is comparator? | A circuit that compares two binary words and indicates whether they are equal is called a comparator | Understand | CO5 | CLO 21 | AEC017.21 |
| 35 | What is ALU? | arithmetic logic unit (ALU) is a digital circuit used to perform arithmetic and logic operations | Remember | CO5 | CLO 21 | AEC017.21 |
| 36 | What is Barrel shifter? | A barrel shifter is a digital circuit that can shift a data word by a specified number of bits without the use of any sequential logic, only pure combinational logic | Remember | CO5 | CLO 19 | AEC017.19 |
| 37 | What is a counter? | Counts those pulses which are driven by a clock. | Understand | CO5 | CLO 19 | AEC017.19 |
| 38 | What are the categories Counters? | (i) Asynchronous and Synchronous counters. (ii) Single and multi mode counters. (iii) Modulus counters. | Remember | CO5 | CLO 19 | AEC017.19 |
| 39 | What is a multimode counter? | If the same counter circuit can be operated in both the UP and DOWN modes, it is called a multimode counters. | Remember | CO5 | CLO 20 | AEC017.20 |
| 40 | What is a asynchronous counters? | Each flip flop is triggered by the previous flip flop. | Understand | CO5 | CLO 22 | AEC017.22 |

Signature of the Faculty

Signature of HOD